

N-Ch MOSFET

General Description

The WSP6044 is the highest performance trench N-ch MOSFETs with extreme high cell density, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

Features

Reliable and Rugged

Lead Free and Green Devices Available

(RoHS Compliant)

Product Summery

BVDSS	RDSON	ID
60V	18m Ω	10A

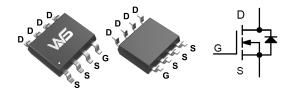
Applications

SMPS Synchronous Rectification.

DC-DC Conversion.

Load Switch.

SOP-8 Pin Configuration



Absolute Maximum Ratings (T= 25 °C Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit	
VDSS	Drain-Source Voltage		60	V	
V _{GSS}	Gate-Source Voltage	±20	V		
TJ	Maximum Junction Temperature		150	°C	
Тѕтс	Storage Temperature Range		-55 to 150	°C	
ls	Diode Continuous Forward Current	T _A =25°C	5	Α	
lo	Continuous Drain Current	T _A =25°C	10		
		T _A =70°C	8		
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	38		
Po	Maximum Power Dissipation	T _A =25°C	3.5	W	
		T _A =70°C	2.2		
RJA ^c	Thermal Resistance-Junction to Ambient	t ≤10s	35	°C/W	
		Steady-State	70		
IASb	Avalanche Current, Single pulse	L=0.1mH	27	А	
EAS ^b	Avalanche Energy, Single pulse	L=0.1mH	36	mJ	

Note a: Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150℃ (initial temperature Tj=25℃).

Note c: Surface Mounted on 1in2 pad area.

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Electrical Characteristics (T= 25 °C unless otherwise noted)

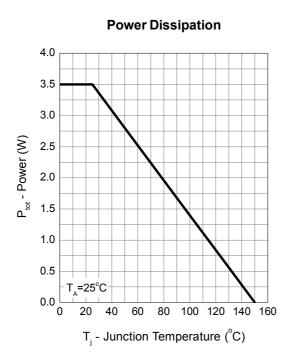
Symbol	Parameter	Test Conditions	Min.	Тур.	Max.	Unit
BVDSS	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250 A	60	-	-	V
Ioss	Zana Oata Valtana Brain Comunit	V _{DS} =48V, V _{GS} =0V	-	-	1	Α
	Zero Gate Voltage Drain Current	TJ=85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250 A	1.4	-	2.4	V
Igss	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
RDS(ON) ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =10A	-	18	25	mΩ
	Diani-Source On-state Resistance	V _{GS} =4.5V, I _{DS} =7A	-	20	30	
Vsd ^d	Diode Forward Voltage	I _{SD} =10A, V _{GS} =0V	-	0.8	1.3	V
trr	Reverse Recovery Time	I _{SD} =10A,	-	21	-	ns
Qrr	Reverse Recovery Charge	dlsp/dt=100A/us	-	22	-	nC
RG	Gate Resistance	V _{GS} =0V,V _{DS} =0V,f=1MHz	-	2.5	-	Ω
Ciss	Input Capacitance	V _{GS} =0V,	-	2370	2780	
Coss	Output Capacitance	V _{DS} =30V,	_	135	-	pF
Crss	Reverse Transfer Capacitance	F=1.0MHz	-	60	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V,	-	14	26	
tr	Turn-on Rise Time	RL=30, Ibs=1A,	-	8	15	ns
td(OFF)	Turn-off Delay Time	V _{GEN} =10V,	_	38	69	
tf	Turn-off Fall Time	R _G =6R	-	12	22	
Qg	Total Gate Charge	V _{DS} =30V, V _{GS} =4.5V, I _{DS} =10A.	-	12	-	
Qg	Total Gate Charge	V _{DS} =30V,	-	26	37	nC
Qgs	Gate-Source Charge	V _{GS} =10V,	-	5	-	
Qgd	Gate-Drain Charge	I _{DS} =10A.	-	5	-	

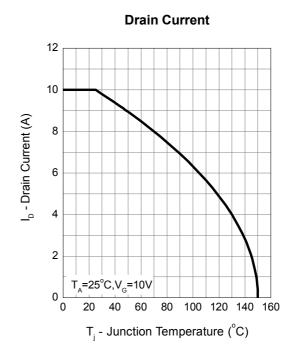
Note d : Pulse test ; pulse width 300us, duty cycle≤2%.

Note e: Guaranteed by design, not subject to production testing.

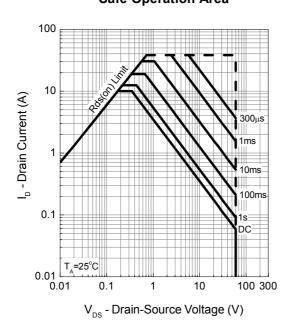


Typical Operating Characteristics

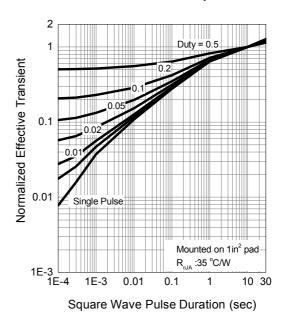




Safe Operation Area



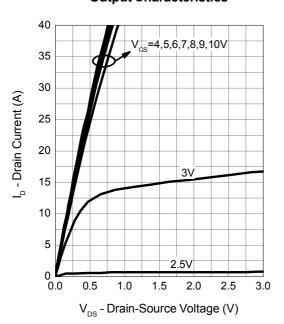
Thermal Transient Impedance



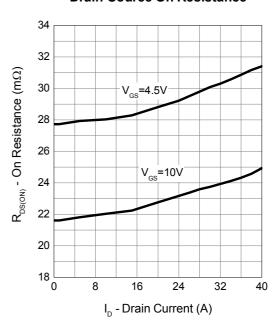


Typical Operating Characteristics (Cont.)

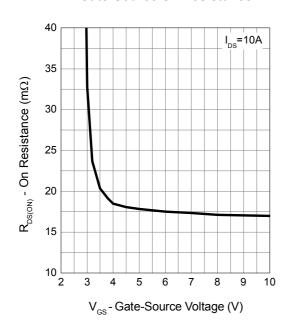
Output Characteristics



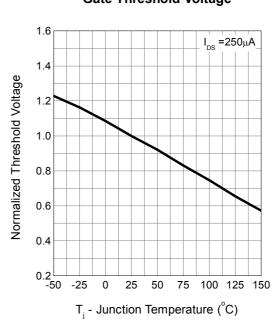
Drain-Source On Resistance



Gate-Source On Resistance



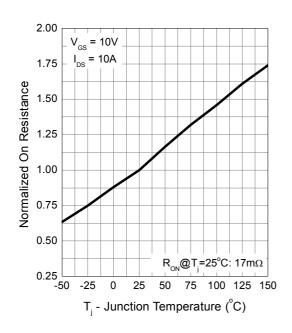
Gate Threshold Voltage



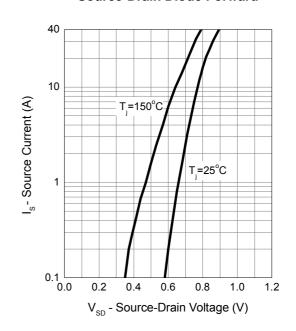


Typical Operating Characteristics (Cont.)

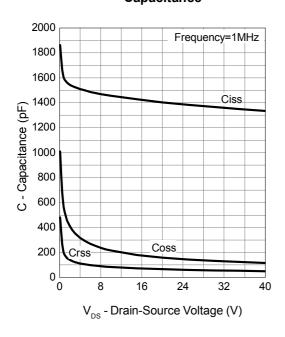
Drain-Source On Resistance



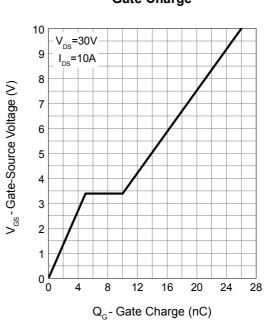
Source-Drain Diode Forward



Capacitance



Gate Charge





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DMN1017UCP3-7 EFC2J004NUZTDG P85W28HP2F-7071 DMN1053UCP4-7 NTE2384 DMC2700UDMQ-7 DMN2080UCB4-7
DMN61D9UWQ-13 US6M2GTR DMN31D5UDJ-7 DMP22D4UFO-7B IPS60R3K4CEAKMA1 DMN1006UCA6-7 DMN16M9UCA6-7
STF5N65M6 IRF40H233XTMA1 STU5N65M6 DMN6022SSD-13 DMN13M9UCA6-7 DMTH10H4M6SPS-13 IPS60R360PFD7SAKMA1
DMN2990UFB-7B SSM3K35CT,L3F IPLK60R1K0PFD7ATMA1 2N7002W-G MCAC30N06Y-TP IPWS65R035CFD7AXKSA1
MCQ7328-TP SSM3J143TU,LXHF DMN12M3UCA6-7 PJMF280N65E1_T0_00201 PJMF380N65E1_T0_00201
PJMF280N60E1 T0 00201 PJMF600N65E1 T0 00201 PJMF900N65E1 T0 00201